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- (71) Applicant (for all designated States except US):
FREESCALE SEMICONDUCTOR INC. [US/US];
6501 William Cannon Drive West, Austin, Texas 78735
(US).
- (72) Inventors; and
- (75) Inventors/Applicants (for US only): **ZHU, Ronghua**
[US/US]; 953 West Nolan Way, Chandler, Arizona 85248
(US). **KHEMKA, Vishnu K.** [IN/US]; 315 E. Mountain
Sky Avenue, Phoenix, Arizona 85048 (US). **BOSE,**

Amitava [US/US]; 6720 South Kenwood Lane, Tempe,
Arizona 85283 (US). **ROGGENBAUER, Todd** [US/US];
902 N. Santa Anna Place, Chandler, Arizona 85224 (US).

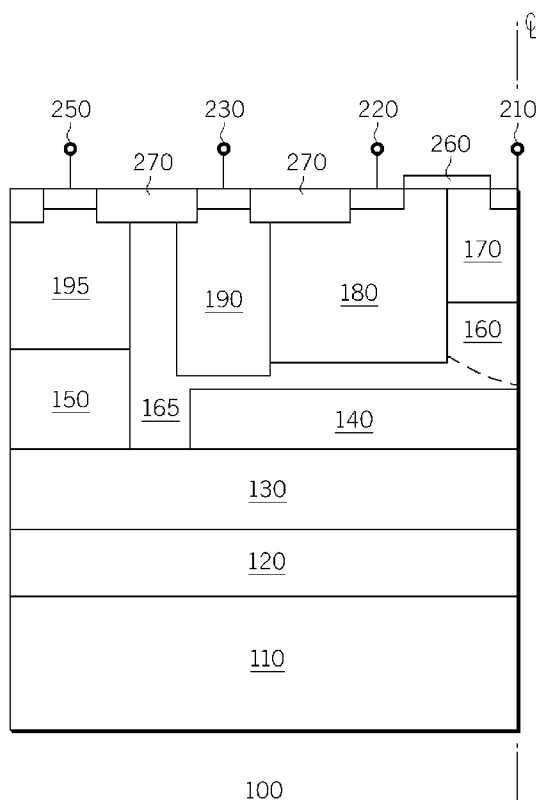
(74) Agents: **KING, Robert L.** et al.; 7700 W. Parmer Lane,
MD:PL02, Austin, Texas 78729 (US).

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(54) Title: ISOLATED ZENER DIODES



(57) Abstract: The present disclosure relates to isolated Zener diodes (100) that are substantially free of substrate current injection when forward biased. In particular, the Zener diodes (100) include an "isolation tub" structure that includes surrounding walls (150, 195) and a base (130) formed of semiconductor regions. In addition, the diodes (100) include silicide block (260) extending between anode (210) and cathode (220) regions. The reduction or elimination of substrate current injection overcomes a significant shortcoming of conventional Zener diodes that generally all suffer from substrate current injection when they are forward biased. Due to this substrate current injection, the current from each of a conventional diode's two terminals is not the same.



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